
1. (Twice Amended) A hybrid semiconductor device, comprising:

a first portion being relatively resistant to breakdown voltage, the first portion comprising a MOS transistor; and

a second portion being less resistant to breakdown voltage and able to survive breakdown without device failure, the second portion residing adjacent the first portion and comprising a diode, wherein the diode has an identical structure as the MOS transistor, except for a source region.

2. (Cancelled)

3. (Cancelled)

4. (Cancelled)

5. (Cancelled)

6. The device of claim 1, where breakdown occurs at a higher voltage in the first portion, and at a lower voltage in the second portion.

7. The device of claim 6, where the breakdown voltage differential is due to a difference in field plate length.

8. The device of claim 7, where the transistor is an SOI- LDMOS device.

9. The device of claim 8, where the transistor is any of an NMOS or PMOS device.

15. A hybrid lateral thin-film Silicon-on-Insulator device comprising:

a first region comprising:

a semiconductor substrate, a buried insulating layer on said substrate, and a lateral MOS device in an SOI layer on said buried insulating layer

and having a source region of a first conductivity type formed in a body region of a second conductivity type opposite to that of the first, a lateral drift region of said first conductivity type adjacent to said body region, a drain region of said first conductivity type and laterally spaced apart from said body region by said lateral drift region, a gate electrode over a part of said body region and over a first part of said lateral drift region adjacent to said body region, said gate electrode being insulated from said body region and drift region by a first insulation region, with a field plate comprised of conducting material extending laterally over said lateral drift region and being electrically connected to said gate electrode; and one or more second regions integrated with the first region, said second regions being identical to the first region, except not comprising said source region, and having a field plate of shorter length than that of the first region.

16. The device of claim 15, where the width of each of the second regions is at least as long as the lateral drift region.

19. (New) A hybrid semiconductor device, comprising:
a first portion being relatively resistant to breakdown; and
a second portion being less resistant to breakdown;
wherein breakdown occurs at a higher voltage in the first portion than in the second portion, and wherein the breakdown voltage differential is due to a

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